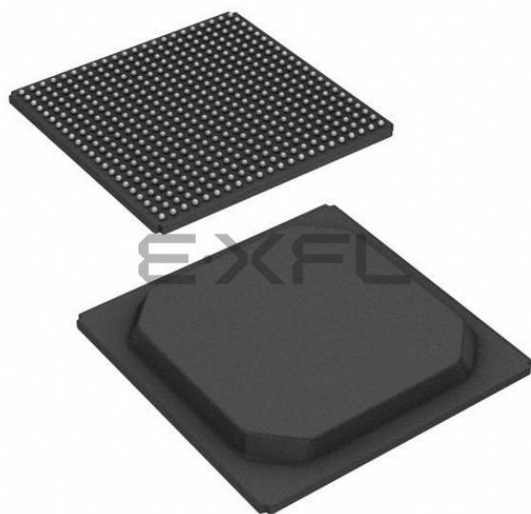




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	244
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300ts-fcg484i

Contents

1	Revision History	1
1.1	Revision 1.3	1
1.2	Revision 1.2	1
1.3	Revision 1.1	1
1.4	Revision 1.0	1
2	Overview	2
3	References	3
4	Device Offering	4
5	Silicon Status	5
6	DC Characteristics	6
6.1	Absolute Maximum Rating	6
6.2	Recommended Operating Conditions	6
6.2.1	DC Characteristics over Recommended Operating Conditions	8
6.2.2	Maximum Allowed Overshoot and Undershoot	8
6.3	Input and Output	12
6.3.1	DC Input and Output Levels	12
6.3.2	Differential DC Input and Output Levels	15
6.3.3	Complementary Differential DC Input and Output Levels	18
6.3.4	HSIO On-Die Termination	19
6.3.5	GPIO On-Die Termination	20
7	AC Switching Characteristics	22
7.1	I/O Standards Specifications	22
7.1.1	Input Delay Measurement Methodology Maximum PHY Rate for Memory Interface IP	22
7.1.2	Output Delay Measurement Methodology	25
7.1.3	Input Buffer Speed	27
7.1.4	Output Buffer Speed	29
7.1.5	Maximum PHY Rate for Memory Interface IP	31
7.1.6	User I/O Switching Characteristics	32
7.2	Clocking Specifications	35
7.2.1	Clocking	35
7.2.2	PLL	36
7.2.3	DLL	37
7.2.4	RC Oscillators	38
7.3	Fabric Specifications	40
7.3.1	Math Blocks	40

7.3.2	SRAM Blocks	41
7.4	Transceiver Switching Characteristics	42
7.4.1	Transceiver Performance	42
7.4.2	Transceiver Reference Clock Performance	42
7.4.3	Transceiver Reference Clock I/O Standards	43
7.4.4	Transceiver Interface Performance	44
7.4.5	Transmitter Performance	44
7.4.6	Receiver Performance	47
7.5	Transceiver Protocol Characteristics	48
7.5.1	PCI Express	48
7.5.2	Interlaken	49
7.5.3	10GbE (10GBASE-R, and 10GBASE-KR)	49
7.5.4	1GbE (1000BASE-T)	50
7.5.5	SGMII and QSGMII	50
7.5.6	SDI	50
7.5.7	CPRI	51
7.5.8	JESD204B	51
7.6	Non-Volatile Characteristics	51
7.6.1	FPGA Programming Cycle and Retention	52
7.6.2	FPGA Programming Time	52
7.6.3	FPGA Bitstream Sizes	53
7.6.4	Digest Cycles	53
7.6.5	Digest Time	54
7.6.6	Zeroization Time	55
7.6.7	Verify Time	57
7.6.8	Authentication Time	58
7.6.9	Secure NVM Performance	58
7.6.10	Secure NVM Programming Cycles	59
7.7	System Services	59
7.7.1	System Services Throughput Characteristics	59
7.8	Fabric Macros	60
7.8.1	UJTAG Switching Characteristics	60
7.8.2	UJTAG_SEC Switching Characteristics	61
7.8.3	USPI Switching Characteristics	62
7.8.4	Tamper Detectors	62
7.8.5	System Controller Suspend Switching Characteristics	64
7.8.6	Dynamic Reconfiguration Interface	64
7.9	Power-Up to Functional Timing	64
7.9.1	Power-On (Cold) Reset Initialization Sequence	64
7.9.2	Warm Reset Initialization Sequence	65
7.9.3	Power-On Reset Voltages	66

3 References

The following documents are recommended references. For more information about PolarFire static and dynamic power data, see the [PolarFire Power Estimator Spreadsheet](#).

- [PO0137](#): PolarFire FPGA Product Overview
- [ER0217](#): PolarFire FPGA Pre-Production Device Errata
- [UG0722](#): PolarFire FPGA Packaging and Pin Descriptions Users Guide
- [UG0726](#): PolarFire FPGA Board Design User Guide
- [UG0686](#): PolarFire FPGA User I/O User Guide
- [UG0680](#): PolarFire FPGA Fabric User Guide
- [UG0714](#): PolarFire FPGA Programming User Guide
- [UG0684](#): PolarFire FPGA Clocking Resources User Guide
- [UG0687](#): PolarFire FPGA 1G Ethernet Solutions User Guide
- [UG0727](#): PolarFire FPGA 10G Ethernet Solutions User Guide
- [UG0748](#): PolarFire FPGA Low Power User Guide
- [UG0676](#): PolarFire FPGA DDR Memory Controller User Guide
- [UG0743](#): PolarFire FPGA Debugging User Guide
- [UG0725](#): PolarFire FPGA Device Power-Up and Resets User Guide
- [UG0677](#): PolarFire FPGA Transceiver User Guide
- [UG0685](#): PolarFire FPGA PCI Express User Guide
- [UG0753](#): PolarFire FPGA Security User Guide
- [UG0752](#): PolarFire FPGA Power Estimator User Guide

6 DC Characteristics

This section lists the DC characteristics of the PolarFire FPGA device.

6.1 Absolute Maximum Rating

The following table lists the absolute maximum ratings for PolarFire devices.

Table 3 • Absolute Maximum Rating

Parameter	Symbol	Min	Max	Unit
FPGA core power supply	V _{DD}	−0.5	1.13	V
Transceiver Tx and Rx lanes supply	V _{DDA}	−0.5	1.13	V
Programming and HSIO receiver supply	V _{DD18}	−0.5	2.0	V
FPGA core and FPGA PLL high-voltage supply	V _{DD25}	−0.5	2.7	V
Transceiver PLL high-voltage supply	V _{DDA25}	−0.5	2.7	V
Transceiver reference clock supply	V _{DD_XCVR_CLK}	−0.5	3.6	V
Global V _{REF} for transceiver reference clocks	XCVR _{VREF}	−0.5	3.6	V
HSIO DC I/O supply ²	V _{DDIx}	−0.5	2.0	V
GPIO DC I/O supply ²	V _{DDIx}	−0.5	3.6	V
Dedicated I/O DC supply for JTAG and SPI	V _{DDI3}	−0.5	3.6	V
GPIO auxiliary power supply for I/O bank x ²	V _{DDAUXx}	−0.5	3.6	V
Maximum DC input voltage on GPIO	V _{IN}	−0.5	3.8	V
Maximum DC input voltage on HSIO	V _{IN}	−0.5	2.2	V
Transceiver Receiver absolute input voltage	Transceiver V _{IN}	−0.5	1.26	V
Transceiver Reference clock absolute input voltage	Transceiver REFCLK V _{IN}	−0.5	3.6	V
Storage temperature (ambient) ¹	T _{STG}	−65	150	°C
Junction temperature ¹	T _J	−55	135	°C
Maximum soldering temperature RoHS	T _{SOLROHS}		260	°C
Maximum soldering temperature leaded	T _{SOLPB}		220	°C

1. See [FPGA Programming Cycles vs Retention Characteristics](#) for retention time vs. temperature. The total time used in calculating the device retention includes storage time and the device stored temperature.
2. The power supplies for a given I/O bank x are shown as V_{DDIx} and V_{DDAUXx}.

6.2 Recommended Operating Conditions

The following table lists the recommended operating conditions.

Table 4 • Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
FPGA core supply at 1.0 V mode ¹	V _{DD}	0.97	1.00	1.03	V
FPGA core supply at 1.05 V mode ¹	V _{DD}	1.02	1.05	1.08	V
Transceiver TX and RX lanes supply at 1.0 V mode (when all lane rates are 10.3125 Gbps or less) ¹	V _{DDA}	0.97	1.00	1.03	V

6.2.2.1 Power-Supply Ramp Times

The following table shows the allowable power-up ramp times. Times shown correspond to the ramp of the supply from 0 V to the minimum recommended voltage as specified in the section [Recommended Operating Conditions](#) (see page 6). All supplies must rise and fall monotonically.

Table 10 • Power-Supply Ramp Times

Parameter	Symbol	Min	Max	Unit
FPGA core supply	V _{DD}	0.2	50	ms
Transceiver core supply	V _{DDA}	0.2	50	ms
Must connect to 1.8 V supply	V _{DD18}	0.2	50	ms
Must connect to 2.5 V supply	V _{DD25}	0.2	50	ms
Must connect to 2.5 V supply	V _{DDA25}	0.2	50	ms
HSIO bank I/O power supplies	V _{DDI} [0,1,6,7]	0.2	50	ms
GPIO bank I/O power supplies	V _{DDI} [2,4,5]	0.2	50	ms
Bank 3 dedicated I/O buffers (GPIO)	V _{DDI3}	0.2	50	ms
GPIO bank auxiliary power supplies	V _{DDAUX} [2,4,5]	0.2	50	ms
Transceiver reference clock supply	V _{DD_XCVR_CLK}	0.2	50	ms
Global V _{REF} for transceiver reference clocks	XCVR _{VREF}	0.2	50	ms

Note: For proper operation of programming recovery mode, if a VDD supply brownout occurs during programming, a minimum supply ramp down time for only the VDD supply is recommended to be 10 ms or longer by using a programmable regulator or on-board capacitors.

6.2.2.2 Hot Socketing

The following table lists the hot-socketing DC characteristics over recommended operating conditions.

Table 11 • Hot Socketing DC Characteristics over Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Current per transceiver Rx input pin (P or N single-ended) ^{1, 2}	XCVR _{RX_HS}			±4	mA	V _{DDA} = 0 V
Current per transceiver Tx output pin (P or N single-ended) ³	XCVR _{TX_HS}			±10	mA	V _{DDA} = 0 V
Current per transceiver reference clock input pin (P or N single-ended) ⁴	XCVR _{REF_HS}			±1	mA	V _{DD_XCVR_CLK} = 0 V
Current per GPIO pin (P or N single-ended) ⁵	I _{GPIO_HS}			±1	mA	V _{DDI_X} = 0 V
Current per HSIO pin (P or N single-ended)						Hot socketing is not supported in HSIO.

1. Assumes that the device is powered-down, all supplies are grounded, AC-coupled interface, and input pin pairs are driven by a CML driver at the maximum amplitude (1 V pk–pk) that is toggling at any rate with PRBS7 data.
2. Each P and N transceiver input has less than the specified maximum input current.
3. Each P and N transceiver output is connected to a 40 Ω resistor (50 Ω CML termination – 20% tolerance) to the maximum allowed output voltage (V_{DDAmax} + 0.3 V = 1.4 V) through an AC-coupling capacitor with all PolarFire device supplies grounded. This shows the current for a worst-case DC coupled interface. As an AC-coupled interface, the output signal will settle at ground and no hot socket current will be seen.
4. V_{DD_XCVR_CLK} is powered down and the device is driven to –0.3 V < V_{IN} < V_{DD_XCVR_CLK}.
5. V_{DDI_X} is powered down and the device is driven to –0.3 V < V_{IN} < GPIO V_{DDI_{max}}.

Table 13 • DC Output Levels

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
PCI ¹	3.15	3.3	3.45		0.1 x V _{DDI}	0.9 x V _{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVC MOS33	3.15	3.3	3.45		0.4	V _{DDI} – 0.4			
LVC MOS25	2.375	2.5	2.625		0.4	V _{DDI} – 0.4			
LVC MOS18	1.71	1.8	1.89		0.45	V _{DDI} – 0.45			
LVC MOS15	1.425	1.5	1.575		0.25 x V _{DDI}	0.75 x V _{DDI}			
LVC MOS12	1.14	1.2	1.26		0.25 x V _{DDI}	0.75 x V _{DDI}			
SSTL25I ³	2.375	2.5	2.625		V _{TT} – 0.608	V _{TT} + 0.608		8.1	8.1
SSTL25II ³	2.375	2.5	2.625		V _{TT} – 0.810	V _{TT} + 0.810		16.2	16.2
SSTL18I ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		6.7	6.7
SSTL18II ³	1.71	1.8	1.89		V _{TT} – 0.603	V _{TT} + 0.603		13.4	13.4
SSTL15I ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL15II ⁴	1.425	1.5	1.575		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
SSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH})/40
SSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /34	(V _{DDI} – V _{OH})/34
HSTL15I	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		8	8
HSTL15II	1.425	1.5	1.575		0.4	V _{DDI} – 0.4		16	16

I/O Standard	V _{DDI} Min (V)	V _{DDI} Typ (V)	V _{DDI} Max (V)	V _{OL} Min (V)	V _{OL} Max (V)	V _{OH} Min (V)	V _{OH} Max (V)	I _{OL} ^{2,6} mA	I _{OH} ^{2,6} mA
HSTL135I ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL135II ⁴	1.283	1.35	1.418		0.2 x V _{DDI}	0.8 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSTL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /50	(V _{DDI} – V _{OH}) /50
HSTL12II ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL18I ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /55	(V _{DDI} – V _{OH}) /55
HSUL18II ⁴	1.71	1.8	1.89		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /25	(V _{DDI} – V _{OH}) /25
HSUL12I ⁴	1.14	1.2	1.26		0.1 x V _{DDI}	0.9 x V _{DDI}		V _{OL} /40	(V _{DDI} – V _{OH}) /40
POD12I ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /48	(V _{DDI} – V _{OH}) /48
POD12II ^{4,5}	1.14	1.2	1.26		0.5 x V _{DDI}			V _{OL} /34	(V _{DDI} – V _{OH}) /34

1. Drive strengths per PCI specification V/I curves.
2. Refer to [UG0686: PolarFire FPGA User I/O User Guide](#) for details on supported drive strengths.
3. For external stub-series resistance. This resistance is on-die for GPIO.
4. I_{OL}/I_{OH} units for impedance standards in amps (not mA).
5. V_{OH_MAX} based on external pull-up termination (pseudo-open drain).
6. The total DC sink/source current of all IOs within a lane is limited as follows:
 - a. HSIO lane: 120 mA per 12 IO buffers.
 - b. GPIO lane: 160 mA per 12 IO buffers.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

6.3.2 Differential DC Input and Output Levels

The follow tables list the differential DC I/O levels.

Table 14 • Differential DC Input Levels

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V _{ICM} ^{1,3} Min (V)	V _{ICM} ^{1,3} Typ (V)	V _{ICM} ^{1,3} Max (V)	V _{ID} ² Min (V)	V _{ID} Typ (V)	V _{ID} Max (V)
LVDS33	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS25	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.35	0.6
		Low	0.05	0.4	0.8	0.1	0.35	0.6
LVDS18 ⁴	GPIO	Mid (default)	0.6	1.25	1.65	0.1	0.35	0.6

Parameter	Description	Min (%)	Typ	Max (%)	Unit	Condition
Single-ended termination to $V_{SS}^{4,5}$	Internal	-20	120	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$
	parallel termination to V_{SS}	-20	240	20	Ω	$V_{DDI} = 2.5\text{ V}/1.8\text{ V}/1.5\text{ V}/1.2\text{ V}$

1. Measured across P to N with 400 mV bias.
2. Thevenin impedance is calculated based on independent P and N as measured at 50% of V_{DDI} .
3. For 50 Ω /75 Ω /150 Ω cases, nearest supported values of 40 Ω /60 Ω /120 Ω are used.
4. Measured at 50% of V_{DDI} .
5. Supported terminations vary with the IO type regardless of V_{DDI} nominal voltage. Refer to Libero for available combinations.

Standard	Description	V_L^1	V_H^1	V_{ID}^2	V_{ICM}^2	$V_{MEAS}^{3,4}$	$V_{REF}^{1,5}$	Unit
SLVS25	SLVS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
SLVS18	SLVS 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.200	0		V
HCSL33	High-speed current steering logic (HCSL) 3.3 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
HCSL25	HCSL 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
HCSL18	HCSL 1.8 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.350	0		V
BLVDSE25 ⁶	Bus LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
MLVDSE25 ⁶	Multipoint LVDS 2.5 V	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
LVPECL33	Low-voltage positive emitter coupled logic	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.650	0		V
LVPECL33 ⁶	Low-voltage positive emitter coupled logic	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.650	0		V
SSTL25I	Differential SSTL 2.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
SSTL25II	Differential SSTL 2.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	1.250	0		V
SSTL18I	Differential SSTL 1.8 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SSTL18II	Differential SSTL 1.8 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.900	0		V
SSTL15	Differential SSTL 1.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
SSTL135	Differential SSTL 1.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL15I	Differential HSTL 1.5 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL15II	Differential HSTL 1.5 V Class II	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.750	0		V
HSTL135I	Differential HSTL 1.35 V Class I	$V_{ICM} - .125$	$V_{ICM} + .125$	0.250	0.675	0		V

Standard	STD	–1	Unit
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL12	1066	1333	Mbps
HSTL12	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMS18 (12 mA)	500	500	Mbps
LVCMS15 (10 mA)	500	500	Mbps
LVCMS12 (8 mA)	300	300	Mbps

1. Performance is achieved with $V_{ID} \geq 200$ mV.

Table 25 • GPIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS25/LVDS33/LCMDS25/LCMDS33	1250	1600	Mbps
RSDS25/RSDS33	800	800	Mbps
MINILVDS25/MINILVDS33	800	800	Mbps
SUBLVDS25/SUBLVDS33	800	800	Mbps
PPDS25/PPDS33	800	800	Mbps
SLVS25/SLVS33	800	800	Mbps
SLVSE15	800	800	Mbps
HCSL25/HCSL33	800	800	Mbps
BUSLVDSE25	800	800	Mbps
MLVDSE25	800	800	Mbps
LVPECL33	800	800	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
HSTL15I	800	900	Mbps
HSTL15II	800	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
PCI	500	500	Mbps
LVTTTL33 (20 mA)	500	500	Mbps
LVCMS33 (20 mA)	500	500	Mbps
LVCMS25 (16 mA)	500	500	Mbps

Standard	STD	–1	Unit
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps
LVC MOS12 (8 mA)	300	300	Mbps
MIPI25/MIPI33	800	800	Mbps

1. All SSTLD/HSTLD/HSULD/LVSTLD/POD type receivers use the LVDS differential receiver.
2. Performance is achieved with $V_{ID} \geq 200$ mV.

7.1.4 Output Buffer Speed

Table 26 • HSIO Maximum Output Buffer Speed

Standard	STD	–1	Unit
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL18I (differential)	800	1066	Mbps
SSTL18II (differential)	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL15I (differential)	1066	1333	Mbps
SSTL15II (differential)	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps
SSTL135I (differential)	1066	1333	Mbps
SSTL135II (differential)	1066	1333	Mbps
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL15I (differential)	900	1100	Mbps
HSTL15II (differential)	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSTL135I (differential)	1066	1066	Mbps
HSTL135II (differential)	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL18II (differential)	400	400	Mbps
HSUL12	1066	1333	Mbps
HSUL12I (differential)	1066	1333	Mbps
HSTL12	1066	1266	Mbps
HSTL12I (differential)	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVC MOS18 (12 mA)	500	500	Mbps
LVC MOS15 (10 mA)	500	500	Mbps

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Clock-to-Data Condition
F _{MAX} 4:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 8:1	RX_DDRX_B_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 2:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 4:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 8:1	RX_DDRX_BL_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
F _{MAX} 2:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered
F _{MAX} 4:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	-1 Min	-1 Typ	-1 Max	Unit	Forwarded Clock-to-Data Skew
Output F _{MAX} 2:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 4:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
Output F _{MAX} 8:1	TX_DDRX_B_C	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered with PLL
In delay, out delay, DLL delay step sizes			12.7	30	35	12.7	25	29.5	ps	

Table 34 • I/O CDR Switching Characteristics

Parameter	Min	Max	Unit
Data rate	266	1250	Mbps
Receiver Sinusoidal jitter tolerance ¹	0.2		UI

1. Jitter values based on bit error ratio (BER) of 10–12, 80 MHz sinusoidal jitter injected to Rx data.

Note: See the LVDS output buffer specifications for transmit characteristics.

7.2 Clocking Specifications

This section describes the PLL and DLL clocking and oscillator specifications.

7.2.1 Clocking

The following table provides clocking specifications.

Table 35 • Global and Regional Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V _{DD} = 1.0 V STD	V _{DD} = 1.0 V –1	V _{DD} = 1.05 V STD	V _{DD} = 1.05 V –1	Unit	Condition
Global clock F _{MAX}	F _{MAXG}	500	500	500	500	MHz	
Regional clock F _{MAX}	F _{MAXR}	375	375	375	375	MHz	Transceiver interfaces only
	F _{MAXR}	250	250	250	250	MHz	All other interfaces
Global clock duty cycle distortion	T _{DCDG}	190	190	190	190	ps	At 500 MHz

Parameter	Symbol	Min	Typ	Max	Unit
Operating current (V_{DD18})	RC_{SCVPP}			0.1	μA
Operating current (V_{DD})	RC_{SCVDD}			60.7	μA

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	33.2	34.9	μs
	MPF300T, TL, TS, TLS	33.2	34.9	μs
	MPF500T, TL, TS, TLS			μs
Factory digest run time	MPF100T, TL, TS, TLS			μs
	MPF200T, TL, TS, TLS	493.6	510.1	μs
	MPF300T, TL, TS, TLS	493.6	510.1	μs
	MPF500T, TL, TS, TLS			μs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6

Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable) ^{1, 3}			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable) ^{1, 4}			ms	One iteration of scrubbing
Time to scrub the fabric data ¹			s	Full scrubbing
Time to scrub the pNVM data (like new) ^{1, 2}			s	Full scrubbing
Time to scrub the pNVM data (recoverable) ^{1, 3}			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable) ^{1, 4}			s	Full scrubbing
Time to verify ⁵			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data ¹			ms	Data erased
Time to destroy data in non-volatile memory (like new) ^{1, 2}			ms	One iteration of scrubbing

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Authenticated text read		113.25	114.02	118.5	μs	
Authenticated and decrypted text read		159.59	160.53	166.5	μs	

Notes:

- Page size= 252 bytes (non-authenticated), 236 bytes (authenticated).
- Only page reads and writes allowed.
- T_{PUF_OVHD} is an additional time that occurs on the first R/W, after cold or warm boot, to sNVM using authenticated or authenticated and encrypted text.

7.6.10 Secure NVM Programming Cycles

The following table describes secure NVM programming cycles.

Table 86 • sNVM Programming Cycles vs. Retention Characteristics

Programming Temperature	Programming Cycles per Page, Max	Programming Cycles per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 bytes. Block size = 56 KBytes.

7.7 System Services

This section describes system switching and throughput characteristics.

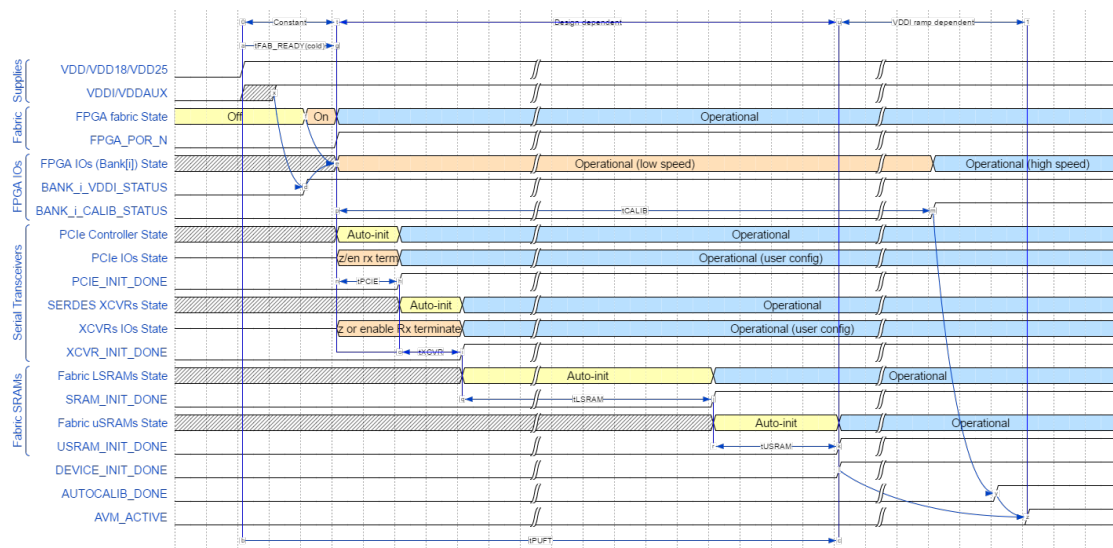
7.7.1 System Services Throughput Characteristics

The following table describes system services throughput characteristics.

Table 87 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Serial number	T_{Serial}	00H	65	67	μs	
User code	T_{User}	01H	0.8	1.05	μs	
Design information	T_{Design}	02H	2.4	2.7	μs	
Device certificate	T_{Cert}	03H	255	271	ms	
Read digests	T_{digest_read}	04H	201	215	μs	
Query security locks	T_{sec_Query}	05H	15	17	μs	
Read debug information	T_{Rd_debug}	06H	34	38	μs	
Reserved		07H–0FH				
Secure NVM write plain text	$T_{SNVM_Wr_Plain}$	10H				Note 1
Secure NVM write authenticated plain text	$T_{SNVM_Wr_Auth}$	11H				Note 1
Secure NVM write authenticated cipher text	$T_{SNVM_Wr_Cipher}$	12H				Note 1
Reserved		13H–17H				

Figure 5 • Cold Reset Timing

**Notes:**

- The previous diagram shows the case where VDDI/VDDAUX of I/O banks are powered either before or sufficiently soon after VDD/VDD18/VDD25 that the I/O bank enable time is measured from the assertion time of VDD/VDD18/VDD25 (that is, the PUFT specification). If VDDI/VDDAUX of I/O banks are powered sufficiently after VDD/VDD18/VDD25, then the I/O bank enable time is measured from the assertion of VDDI/VDDAUX and is not specified by the PUFT specification. In this case, I/O operation is indicated by the assertion of BANK_i_VDDI_STATUS, rather than being measured relative to FABRIC_POR_N negation.
- AUTOCALIB_DONE assertion indicates the completion of calibration for any I/O banks specified by the user for auto-calibration. AUTOCALIB_DONE asserts independently of DEVICE_INIT_DONE. It may assert before or after DEVICE_INIT_DONE and is determined by the following:
 - How long after VDD/VDD18/VDD25 that VDDI/VDDAUX are powered on. Note that if any of the user-specified I/O banks are not powered on within the auto-calibration timeout window, then AUTOCALIB_DONE doesn't assert until after this timeout.
 - The specified ramp times of VDDI of each I/O bank designated for auto-calibration.
 - How much auto-initialization is to be performed for the PCIe, SERDES transceivers, and fabric LSRAMs.
- If any of the I/O banks specified for auto-calibration do not have their VDDI/VDDAUX powered on within the auto-calibration timeout window, then it will be approximately auto-calibrated whenever VDDI/VDDAUX is subsequently powered on. To obtain an accurate calibration however, on such IO banks, it is necessary to initiate a re-calibration (using CALIB_START from fabric).
- AVM_ACTIVE only asserts if avionics mode is being used. It is asserted when the later of DEVICE_INIT_DONE or AUTOCALIB_DONE assert.

7.9.2**Warm Reset Initialization Sequence**

The following warm reset timing diagram shows the initialization sequencing of the device when either DEVRST_N or TAMPER_RESET_DEVICE signals are asserted.

7.9.4 Design Dependence of T_{PUFT} and T_{WRFT}

Some phases of the device initialization are user design-dependent, as the device automatically initializes certain resources to user-specified configurations if those resources are used in the design. It is necessary to compute the overall power-up to functional time by referencing the following tables and adding the relevant phases, according to the design configuration. The following equation refers to timing parameters specified in the above timing diagrams. Please note T_{PCIE} , T_{XCVR} , T_{LSRAM} , and T_{USRAM} can be found in the PolarFire FPGA device power-up and resets user guide UG0725.

$$T_{PUFT} = T_{FAB_READY(cold)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$$

$$T_{WRFT} = T_{FAB_READY(warm)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$$

Note: T_{PCIE} , T_{XCVR} , T_{LSRAM} , T_{USRAM} , and T_{CALIB} are common to both cold and warm reset scenarios.

Auto-initialization of FPGA (if required) occurs in parallel with I/O calibration. The device may be considered fully functional only when the later of these two activities has finished, which may be either one, depending on the configuration, as may be calculated from the following tables. Note that I/O calibration may extend beyond T_{PUFT} (as I/O calibration process is independent of main device power-on and is instead dependent on I/O bank supply relative power-on time and ramp times). The previous timing diagram for power-on initialization shows the earliest that I/Os could be enabled, if the I/O power supplies are powered on before or at the same time as the main supplies.

7.9.5 Cold Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the power supplies reaching the above trip point levels until the FPGA fabric is operational and the FPGA I/Os are functional for low-speed (sub 400 MHz) operation.

Table 99 • Cold Boot

Power-On (Cold) Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – $T_{IN_ACTIVE(cold)}$	1.17	4.51	7.84	ms
Time when weak pull-ups are enabled – $T_{PU_PD_ACTIVE(cold)}$	1.17	4.51	7.84	ms
Time when fabric is operational – $T_{FAB_READY(cold)}$	1.20	4.54	7.87	ms
Time when output pins start driving – $T_{OUT_ACTIVE(cold)}$	1.22	4.56	7.89	ms

7.9.6 Warm Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the negation of the warm reset event until the FPGA fabric is operational and the FPGA I/Os are functional for low-speed (sub 400 MHz) operation.

Table 100 • Warm Boot

Warm Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – $T_{IN_ACTIVE(warm)}$	0.91	1.76	2.62	ms
Time when weak pull-ups/pull-downs are enabled – $T_{PU_PD_ACTIVE(warm)}$	0.91	1.76	2.62	ms
Time when fabric is operational – $T_{FAB_READY(warm)}$	0.94	1.79	2.65	ms
Time when output pins start driving – $T_{OUT_ACTIVE(warm)}$	0.96	1.81	2.67	ms

7.9.7 Miscellaneous Initialization Parameters

In the following table, T_{FAB_READY} refers to either $T_{FAB_READY(cold)}$ or $T_{FAB_READY(warm)}$ as specified in the previous tables, depending on whether the initialization is occurring as a result of a cold or warm reset, respectively.

1. With DPA counter measures.

Table 115 • HMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
HMAC-SHA-256 ¹ , 256-bit key	512	7477	2361
	64K	88367	2099
HMAC-SHA-384 ¹ , 384-bit key	1024	13049	2257
	64K	106103	2153

1. With DPA counter measures.

Table 116 • CMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-CMAC-256 ¹ (message is only authenticated)	128	446	9058
	64K	45494	111053

1. With DPA counter measures.

Table 117 • KEY TREE

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
128-bit nonce + 8-bit optype		102457	2751
256-bit nonce + 8-bit optype		103218	2089

Table 118 • SHA

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
SHA-1 ¹	512	2386	1579
	64K	77576	990
SHA-256 ¹	512	2516	884
	64K	84752	938
SHA-384 ¹	1024	4154	884
	64K	100222	938
SHA-512 ¹	1024	4154	881
	64K	100222	935

1. With DPA counter measures.

Table 119 • ECC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
ECDSA SigGen, P-384/SHA-384 ¹	1024	12528912	6944
	8K	12540448	5643
ECDSA SigGen, P-384/SHA-384	1024	5502928	6155

SigVer, DSA-2048/SHA-256	1024	9810527	10884
	8K	9597000	10719
Key Agreement (KAS), DH-3072 (p=3072, security=256)		4920705	9338
Key Agreement (KAS), DH-3072 (p=3072, security=256) ¹		78914533	9083

1. With DPA counter measures.

Table 122 • NRBG

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
Instantiate: strength, s=256, 384-bit nonce, 384-bit personalization string		18221	2841
Reseed: no additional input, s=256		13585	1180
Reseed: 384-bit additional input, s=256		15922	1342
Generate: (no additional input), prediction resistance enabled, s= 256	128	15262	1755
	8K	27169	8223
Generate: (no additional input), prediction resistance disabled, s= 256	128	2138	1167
	8K	14045	8223
Generate: (384-bit additional input), prediction resistance enabled, s= 256	128	21299	1944
	8K	33206	8949
Generate: (384-bit additional input), prediction resistance disabled, s= 256	128	11657	1894
	8K	23564	8950
Un-instantiate		761	666

1. With DPA counter measures.